	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e	r D e f i	r r o r
1	BRS	34 6	non adj volatile near memory and float\$4 adj gate with silicon near nitride and control\$4 adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 21:19	***************************************		Ο
2	BRS	21 2	non adj volatile near memory and float\$4 adj gate with silicon near nitride and control\$4 adj gate with	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 21:30			Ο
3	BRS	1	gate with silicon near nitride and control\$4 adj gate with oxide with	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 21:23			Ο
4	BRS		-	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 21:23			0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e n	D f i n	Error
5	BRS	0	gate with silicon near nitri\$8 with nh3 and control\$4 adj	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 21:32			0
6	BRS	0	non adj volatile near memory and float\$4 adj gate with nitri\$8 with nh3 and control\$4 adj gate with	1	2004/03/08 21:32			0
7	BRS	0	memory and float\$4 adj gate with nitri\$8 with nh3 and control\$4 adj gate with	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 21:32			0
8	BRS	3	Memdry and float\$4 adj gate same nitri\$8 with nh3 and control\$4 adj gate with oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 21:58			0

	ТУр	Hi ts	Search Text	DBs	Time Stamp	m m e	r D e f i n	o r
9	BRS	0	nh3 and	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 21:59			0
10	BRS	0	nh3 and control\$4 adj	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 22:00			Ο
11	BRS	13	memory and float\$4 adj gate and rtn and control\$4 adj gate and (tantalum or titanium) with oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 22:44			0
12	BRS	2	-	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 22:46			0
13	BRS	1	6300664.URPN.	USPAT	2004/03/08 22:45			0

	Тур e	Hi	Search Text	DBs	Time Stamp	m m e n	r D e f i n	r
14	BRS		memory and float\$4 adj gate with nitr\$8 and control\$4 adj gate and (tantalum or titanium) with oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 22:47			О
15	BRS		memory and float\$4 adj gate with nitr\$8 and control\$4 adj gate with (tantalum or titanium) with oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 16:31			Ο
16	BRS		memory and float\$4 adj gate with nitr\$8 and control\$4 adj gate with (tantalum or titanium) with oxide and nh3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 22:54			0
17	BRS		memory and float\$4 adj gate with nitr\$8 and control\$4 adj gate with (tantalum or titanium) with oxide and rtn	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 22:55			0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e	ErrorDefinitio	
18	BRS	4		USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/08 22:56			Ο
19	BRS	23 0	4698787.URPN.	USPAT	2004/03/08 22:58			0
20	BRS	5	4698787.URPN. and rtn	USPAT	2004/03/08 22:59			0
21	BRS	66	float\$4 adj gate same nitriding	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/09 15:36			0
22	BRS	38	float\$4 adj gate with nitriding	世島野A早身B US-PGPUB; EPO; JPO; DERWENT;	2004/03/09 14:48			0
23	BRS	8	float\$4 adj gate with nitriding with silicon adj nitride	IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 15:13			0
24	BRS	0	float\$4 adj gate with nitridi\$7 with silicon adj nitride and tantalum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 15:14			0
25	BRS	U j	float\$4 adj gate with nitrida\$7 with silicon adj nitride and tantalum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 15:14			0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m m e	D e f	Ennons
26	BRS	10	float\$4 adj gate with nitridi\$7 with silicon adj nitride		2004/03/09 15:22			0
27	BRS	21	float\$4 adj gate same nitridi\$7 same silicon adj nitride		2004/03/09 15:22			0
28	BRS	0	nitridi\$7 same silicon adj		2004/03/09 15:23			0
29	BRS		nitrida\$7 same	1	2004/03/09 15:26			0
30	BRS	1	float\$4 adj gate with nitrida\$7 and nitride with tantalum	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 15:27			0
31	BRS	47 75	float\$4 adj gate same nitri\$8	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/09 15:36			0
32	BRS	29 33	float\$4 adj gate with nitri\$8	世島坪 <u>入</u> 罪身B US-PGPUB; EPO; JPO; DERWENT;	2004/03/09 15:36			0
33	BRS	51	float\$4 adj gate with nitri\$8 and silicon adj nitride with tantalum	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 15:37	1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1		0

	Тур	Hi	Search Text	DBs	Time Stamp	m m e	r D e f i	o r
34	BRS	46	float\$4 adj gate with nitri\$8 and silicon adj nitride with tantalum and control\$4 adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 15:45			0
35	BRS	0	float\$4 adj gate with nitri\$8 with (nh3 or ammonia) and silicon adj nitride with tantalum and control\$4 adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 15:46			0
36	BRS	0	or n2o) and silicon adj nitride with tantalum and control\$4 adj	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 15:47			0
37	BRS	0	gate float\$4 adj gate with nitri\$8 same (nh3 or ammonia or nitrogen or n2 or n2o) and silicon adj nitride with tantalum and control\$4 adj	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/09 15:48			0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m m	r D e f i	Errors
38	BRS	16	or n2o) and silicon adj nitride with tantalum and control\$4 adj		2004/03/09 15:48			0
39	BRS	44	float\$4 adj gate with (nitridiZ\$8 or nitridat\$8 or nitrif\$8) and control\$4 adj gate		2004/03/10 14:10			0
	BRS		float\$4 adj gate with (nitridiz\$8 or nitridat\$8 or nitrif\$8) and control\$4 adj gate and (tantalum or ta2o5)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/10 13:47			0
41	IS& R	2	("5600166").PN	JPO; DERWENT;	2004/03/10 13:48			0
42	BRS	11	5600166.URPN.	IBM TDB USPAT	2004/03/10 13:48			0
43	BRS	5	float\$4 adj gate with (nitridiZ\$8 or nitridat\$8 or nitrif\$8) with silicon adj nitride and control\$4 adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/10 14:20			0

	Тур	Hi ts	Search Text	DBs	Time Stamp	m e n	r D e f i n	r r o r
44	BRS	52	float\$4 adj gate and \$5silicon with (nitridiZ\$8 or nitridat\$8 or nitrif\$8) with silicon adj nitride and control\$4 adj gate	US-PGPUB; EPO;	2004/03/10 14:21			0
45	BRS		float\$4 adj gate and \$5silicon with (nitridiZ\$8 or nitridat\$8 or nitrif\$8) with silicon adj nitride and control\$4 adj gate and (tantalum or ta2o5) with oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/10 14:21			0